

1 divisional application of U.S. Patent Application Serial No. 08/742,895,  
2 filed November 1, 1996. <sup>U.S. Pat. No. 5,998,256</sup>

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4 In the Claims:

5 Cancel claims 1-50.  
6

7 New Claims

8 51. A method of forming a plurality of DRAM capacitors  
9 comprising:

10 etching capacitor container openings for an array in a substrate in  
11 at least two separate etching steps, and forming electrically insulative  
12 partitions between adjacent capacitors intermediate the two etching steps.

13  
14 52. The method of claim 51 wherein the forming electrically  
15 insulative partitions step comprises:

16 forming insulative material over the substrate; and  
17 conducting an anisotropic etch of the insulative material to a  
18 degree sufficient to leave the partitions.  
19

20 53. A processing method of forming a plurality of DRAM  
21 capacitors comprising etching capacitor container openings for a capacitor  
22 array in a substrate in two separate etching steps.  
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